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APPLICATION

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APPLICANT: Yang et al.	
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	Michaelson, "The work function of the elements and its periodicity", <i>JOURNAL OF APPLIED PHYSICS</i> , Vol. 48, No. 11, November 1977, pp.4729-4733.
	Zlatanovic et al., "Variation of reflectivity spectra, preferred orientation and stoichiometry of polycrystalline TiN films due to nitrogen flow variation" <i>PROC. 22nd INTERNATIONAL CONFERENCE ON MICROELECTRONICS (MIEL 2000)</i> , Vol. 1, NIS, SERBIA, 14-17, May 2000, pp. 261-264.
	Farahani et al., "Limitation of the Tin/ Ti layer formed by the rapid thermal heat treatment of pure Ti films in an NH <sub>3</sub> ambient in fabrication of submicrometer CMOS flash EPROM IC's", <i>IEEE TRANSACTIONS ON SEMICONDUCTOR MANUFACTURING</i> , Vol. 10, No. 1, February 1997, pp.147-153.
	Abc et al. "Cu damascene interconnects with crystallographic texture control and its electromigration performance", <i>IEEE 98CH36173. 36<sup>th</sup> ANNUAL INTERNATIONAL RELIABILITY PHYSICS SYMPOSUMS</i> , RENO, NEVADA, 1998, pp.342-347.
	Sun et al. "A comparative study of CVD TiN and CVD TaN diffusion barriers for copper interconnection", 1995, pp. 18. 5.1-18. 5. 4.

EXAMINER	DATE CONSIDERED
Dh	12/2005

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